

IN THE CLAIMS

Please amend the claims as follows:

1. (Currently Amended) A multilevel wiring interconnect in an integrated circuit, comprising:
 - a number of multilayer metal lines connecting to a number of silicon devices in a substrate;
 - a low dielectric constant insulator in a number of interstices between the number of multilayer metal lines and the substrate;
 - wherein the low dielectric constant insulator includes a number of air gaps in the low dielectric constant material; and
 - wherein the low dielectric constant insulator includes a film in which of a set of methyl groups and a fluorine group of atoms are as much as 43% and 9% respectively of that for a content of silicon atoms in the film.
2. (Original) The multilevel wiring interconnect of claim 1, wherein the low dielectric constant insulator includes a low dielectric constant organic silica film.
3. (Original) The multilevel wiring interconnect of claim 1, wherein the low dielectric constant insulator includes a low dielectric constant insulator having a dielectric constant (k) of less than 2.7.
4. (Canceled).
5. (Original) The multilevel wiring interconnect of claim 1, wherein the number of multilayer metal lines includes a number of multilayer metal lines selected from the group consisting of Aluminum, Copper, Silver, and Gold.

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6. (Original) The multilevel wiring interconnect of claim 1, wherein the number of multilayer metal lines includes a first conductor bridge level.
7. (Currently Amended) A multilevel wiring interconnect system, comprising:
a number of multilayer metal lines connecting to a number of integrated circuit devices in a substrate;
a low dielectric constant insulator in a number of interstices between the number of multilayer metal lines and the substrate, the low dielectric constant insulator having a number of air gaps therein; and
wherein the low dielectric constant insulator includes a film in which of a set of methyl groups and a fluorine group of atoms are as much as 43% and 9% respectively of that for a content of silicon atoms in the film.
8. (Original) The system of claim 7, wherein the number of multilayer metal lines are adapted to connect to at least one of a processor and a memory.
9. (Original) The system of claim 7, wherein the substrate is a die.
10. (Original) The system of claim 7, wherein the substrate includes a silicon.
11. (Original) The system of claim 7, wherein the number of multilayer metal lines consist essentially of copper.
12. (Withdrawn) A system having a multilevel wiring interconnect, comprising:
an integrated circuit device; and
an integrated memory circuit operably coupled to the integrated circuit device, wherein the integrated memory circuit includes a multilevel wiring interconnect, the multilevel wiring interconnect comprising:
a number of multilayer Copper lines connecting to one or more of the transistors in the substrate;

a low dielectric constant insulator in a number of interstices between the number of multilayer Copper lines and the substrate;

wherein the low dielectric constant insulator includes a number of air gaps in the low dielectric constant material; and

wherein the low dielectric constant insulator includes a film in which of a set of methyl groups and a fluorine group of atoms are as much as 43% and 9% respectively of that for a content of silicon atoms in the film.

13. (Withdrawn) The system of claim 12, wherein the integrated circuit device includes a processor.

14. (Withdrawn) A system, comprising:

a processor; and

an integrated memory circuit coupled to the processor, wherein the integrated memory circuit further includes a multilevel wiring interconnect, the multilevel wiring interconnect comprising:

a number of multilayer Copper lines connecting to one or more of the transistors in the substrate;

a low dielectric constant insulator in a number of interstices between the number of multilayer Copper lines and the substrate;

wherein the low dielectric constant insulator includes a number of air gaps in the low dielectric constant material; and

wherein the low dielectric constant insulator includes a film in which of a set of methyl groups and a fluorine group of atoms are as much as 43% and 9% respectively of that for a content of silicon atoms in the film.

15. (Withdrawn) The system of claim 14, wherein the low dielectric constant insulator includes a low dielectric constant organic silica film.

16. (Withdrawn) The system of claim 14, wherein the low dielectric constant insulator includes a low dielectric constant insulator having a dielectric constant of less than 2.7.

17. (Canceled).